

1700V 3A N-Channel SiC MOSFET

Features

- · Low On-Resistance
- · Low Capacitance
- Avalanche Ruggedness
- · Halogen Free, RoHS Compliant

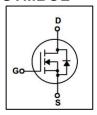
BENEFITS

- Higher System Efficiency
- Parallel Device Convenience
- High Temperature Application
- High Frequency Operation

Application

- Switch Mode Power Supply (SMPS)
- Power Factor Correction (PFC)
- Uninterruptible Power Supply (UPS)
- EV Charging station & Motor Drives
- · Solar/ Wind Renewable Energy
- Power Inverters & DC/DC Converters

SYMBOL





ASSEMBLY MESSAGE

| Product Name | Package | Packaging |
|--------------|---------|-----------|
| BXW3M1K7H | TO-247 | Tube |

ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

| Parameter | | Symbol | Rating | Unit |
|--|--------------------------------|----------------------------------|-------------|------|
| | | Cymico. | TO-247 | |
| Drain-Source Voltage | | V _{DSS} | 1700 | V |
| Continuous Drain Current | T _C = 25°C, VGS=20V | ID | 3 | Α |
| Single Pulse Avalanche Energy | L=10mH | Eas | 88 | mJ |
| | L=10mH | IAS | 4.2 | Α |
| Pulsed Drain Current | | I _{DM} | 12 | Α |
| Recommend Gate Source Voltage(Static) | | V _{GS} ,op | -3/+20 | V |
| Maximum Gate Source Voltage(AC (f > 1Hz)) | | V _{GS,} max | -5/+25 | V |
| Power Dissipation | T _C =25°C | P _D | 69 | W |
| Soldering Temperature | | TL | 260 | °C |
| Operating Junction and Storage Temperature Range | | T _J ,T _{STG} | 150,-55~150 | °C |
| Thermal Resistance, Junction to Case | | R _{θJC} | 1.81 | °C/W |



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ELECTRICAL CHARACTERISTICS (T_J=25°C,unless otherwise Noted)

| Parameter | Symbol | Test Condition | Min. | Тур. | Max. | Unit | |
|------------------------------------|----------------------|---------------------------|------|------|------|------|--|
| OFF CHARACTERISTICS | • | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | VGS=0V, ID=250µA | 1700 | | | V | |
| Zero Gate Voltage Drain Current | I _{DSS} | VDS=1200V, VGS=0V | | | 10 | uA | |
| Gate-Body Leakage Current, Forward | I _{GSS} | VGS=20V,VDS = 0V | | | 250 | nA | |
| ON CHARACTERISTICS | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | VDS=10V, ID=1mA | 2.5 | | 4.5 | V | |
| Drain-Source On-State Resistance | Rds(on) | VGS=20V, ID=1.5A | | 1.1 | 1.32 | Ω | |
| | | VGS=18V, ID=1.5A | | 1.14 | 1.37 | | |
| | | VGS=15V, ID=1.5A | | 1.23 | 1.48 | | |
| | | VGS=20V, ID=1.5A, TJ=150℃ | | 1.69 | | | |
| DYNAMIC PARAMETERS | | | | | | | |
| Input Capacitance | C _{ISS} | \/D0_4000\/\/00_0\/ | | 125 | | pF | |
| Output Capacitance | Coss | VDS=1000V,VGS=0V, | | 17.6 | | pF | |
| Reverse Transfer Capacitance | Crss | f=1MHz,VAC=25mV | | 4.4 | | pF | |
| SWITCHING PARAMETERS | • | | | | | | |
| Total Gate Charge(Note2) | Q_{G} | | | 15 | | nC | |
| Gate Source Charge | Q _{GS} | VDS =1200V, | | 3 | | nC | |
| Gate Drain Charge | Q _{GD} | VGS =-3/+20 V, ID=3A | | 9 | | nC | |
| Gate plateau voltage | V_{pl} | | | 7.2 | | V | |
| Turn-ON Delay Time | t _{D(ON)} | | | 36 | | ns | |
| Turn-ON Rise Time | t _R | VDS=800V, ID=3A, | | 55 | | ns | |
| Turn-OFF Delay Time | t _{D(OFF)} | VGS = -3/+20 V ,RG=25Ω | | 30 | | ns | |
| Turn-OFF Fall-Time | t _F | | | 46 | | ns | |
| Internal Gate Resistance | R _{G(int.)} | f =1MHz, VAC=25mV | | 6 | | Ω | |
| SOURCE- DRAIN DIODE RATINGS | AND CHA | RACTERISTICS | | | • | | |
| Drain-Source Diode Forward Voltage | V _{SD} | IS=1.5A, VGS=-3V | | 5.5 | | V | |
| Continuous Diode Forward Current | Is | VGS = -3V | | 3 | | Α | |
| Reverse Recovery Time | t _{rr} | VGS = -3/+20V,IF = 3A, | | 8 | | ns | |
| Reverse Recovery Charge | Qrr | VDS=400V, | | 5.5 | | nC | |
| Peak Reverse Recovery Current | I _{rrm} | di/dt =300A /µs | | 1 | | А | |



TYPICAL CHARACTERISTICS

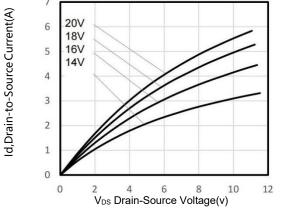


Figure 1. Typical Output Characteristics

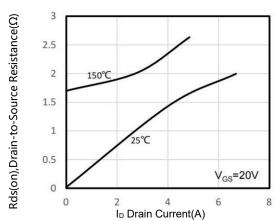


Figure 3. On-Resistance versus Drain Current

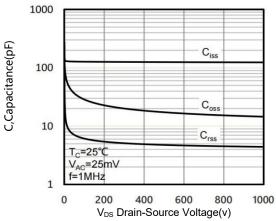


Figure 5. Typical Capacitance versus V_{DS}

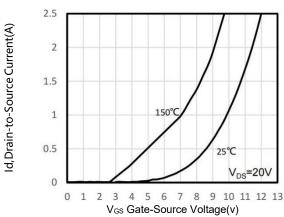


Figure 2. Typical Transfer Characteristics

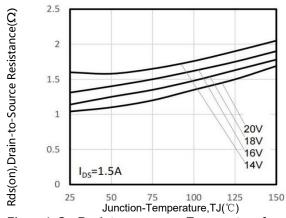


Figure 4. On-Resistance versus Temperature for Various Gate Voltage

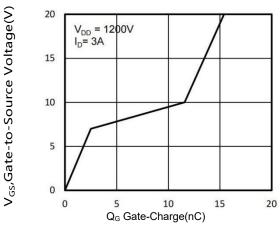


Figure 6. Typical Gate Charge versus V_{GS}



TYPICAL CHARACTERISTICS(Cont.)

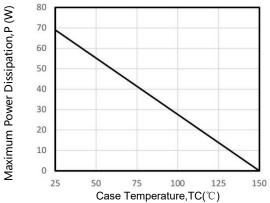
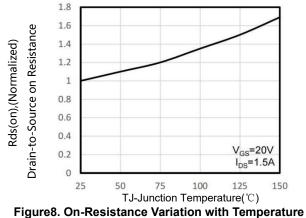


Figure 7. Maximum Power Dissipation Derating versus Case Temperature



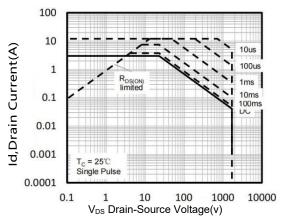


Figure 9. Maximum Safe Operating Area

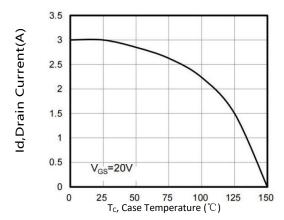


Figure 10. Maximum Continuous Drain Current versus Case Temperature

Version: 1.0

Revision history

Document revision history

| Date | Revision | Changes |
|-------------|----------|---------------|
| 12-Mar-2022 | 1.0 | First release |
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